



FDMS4D0N12C

N PowerTrench® MOSFET120V118A4.0mΩ

N MV MOSFET PowerTrench®

- Shielded Gate MOSFET Technology
 - Max rDS(on) = 4.0 mΩ at VGS = 10 V, ID = 67 A
 - Max rDS(on) = 8.0 mΩ at VGS = 6 V, ID = 33 A
 - 50% Lower Qrr than Other MOSFET Suppliers
 - Lowers Switching Noise/EMI
 - MSL1 Robust Package Design
 - 100% UIL Tested
 - RoHS Compliant
- This product is general usage and suitable for many different applications.
 - AC-DC and DC-DC Power Supplies

	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DS(BR)} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
FDMS4D0N12C	2.141	 	Active	N-Channel	Single	120	+20V	4	118	2.7			4		58	4565	PQFN-8